

General Description

These N-channel MOSFET are produced using advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

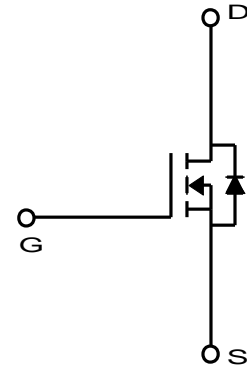
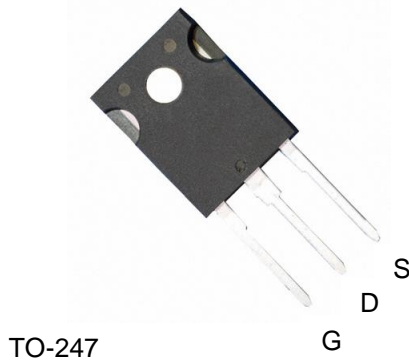
These devices are suitable device for SMPS, high Speed switching and general purpose applications.

Features

- $V_{DS} = 500V$
- $I_D = 23A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 0.245\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- HID
- Lighting



Absolute Maximum Ratings ($T_a = 25^\circ C$)

| Characteristics | Symbol | Rating | Unit |
|--|----------------|---------------------------|------------|
| Drain-Source Voltage | V_{DSS} | 500 | V |
| Gate-Source Voltage | V_{GSS} | ± 30 | V |
| Continuous Drain Current | I_D | $T_C=25^\circ C$ | 23 |
| | | $T_C=100^\circ C$ | 14.6 |
| Pulsed Drain Current ⁽¹⁾ | I_{DM} | 92 | A |
| Power Dissipation | P_D | $T_C=25^\circ C$ | 290 |
| | | Derate above $25^\circ C$ | 2.33 |
| Repetitive Avalanche Energy ⁽¹⁾ | E_{AR} | 29 | mJ |
| Peak Diode Recovery dv/dt ⁽³⁾ | dv/dt | 4.5 | V/ns |
| Single Pulse Avalanche Energy ⁽⁴⁾ | E_{AS} | 950 | mJ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55~150 | $^\circ C$ |

* I_D limited by maximum junction temperature

Thermal Characteristics

| Characteristics | Symbol | Rating | Unit |
|--|-----------------|--------|--------------|
| Thermal Resistance, Junction-to-Ambient ⁽¹⁾ | $R_{\theta JA}$ | 40 | $^\circ C/W$ |
| Thermal Resistance, Junction-to-Case ⁽¹⁾ | $R_{\theta JC}$ | 0.44 | |

Ordering Information

| Part Number | Temp. Range | Package | Packing | RoHS Status |
|-------------|-------------|---------|---------|--------------|
| MDQ23N50DTP | -55~150°C | TO-247 | Tube | Pb Free |
| MDQ23N50DTH | -55~150°C | TO-247 | Tube | Halogen Free |

Electrical Characteristics (Ta =25°C)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|---------------------|--|-----|------|-------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | I _D = 250μA, V _{GS} = 0V | 500 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 2.0 | - | 4.0 | V |
| Drain Cut-Off Current | I _{DSS} | V _{DS} = 500V, V _{GS} = 0V | - | - | 1 | μA |
| Gate Leakage Current | I _{GSS} | V _{GS} = ±30V, V _{DS} = 0V | - | - | 100 | nA |
| Drain-Source ON Resistance | R _{DS(ON)} | V _{GS} = 10V, I _D = 11.5A | - | 0.2 | 0.245 | Ω |
| Forward Transconductance | g _{fs} | V _{DS} = 30V, I _D = 11.5A | - | 13 | - | S |
| Dynamic Characteristics | | | | | | |
| Total Gate Charge | Q _g | V _{DS} = 400V, I _D = 23A, V _{GS} = 10V | - | 76 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 16 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 20 | - | |
| Input Capacitance | C _{iSS} | V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz | - | 3280 | - | pF |
| Reverse Transfer Capacitance | C _{rSS} | | - | 23 | - | |
| Output Capacitance | C _{oss} | | - | 325 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{GS} = 10V, V _{DS} = 250V, I _D = 23A, R _G = 25Ω | - | 50 | - | ns |
| Rise Time | t _r | | - | 155 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 230 | - | |
| Fall Time | t _f | | - | 195 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Maximum Continuous Drain to Source Diode Forward Current | I _S | | - | - | 23 | A |
| Source-Drain Diode Forward Voltage | V _{SD} | I _S = 23A, V _{GS} = 0V | - | - | 1.4 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 23A, di/dt = 100A/μs ⁽³⁾ | - | 450 | - | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | - | 6 | - | μC |

Notes :

- Pulse width is based on R_{θJC} & R_{θJA} and the maximum allowed junction temperature of 150°C.
- Pulse test: pulse width ≤300us, duty cycle ≤2%, pulse width limited by junction temperature T_{J(MAX)}=150°C.
- I_{SD} ≤23A, di/dt ≤200A/us, V_{DD} ≤BV_{DSS}, R_G =25Ω, Starting T_J=25°C
- L=3.24mH, I_{AS}=23A, V_{DD}=50V, R_G =25Ω, Starting T_J=25°C

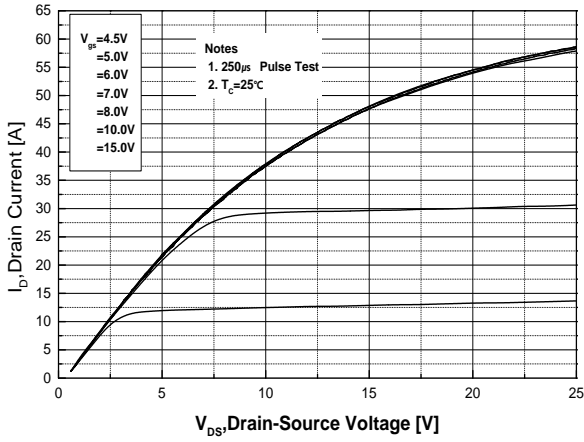


Fig.1 On-Region Characteristics

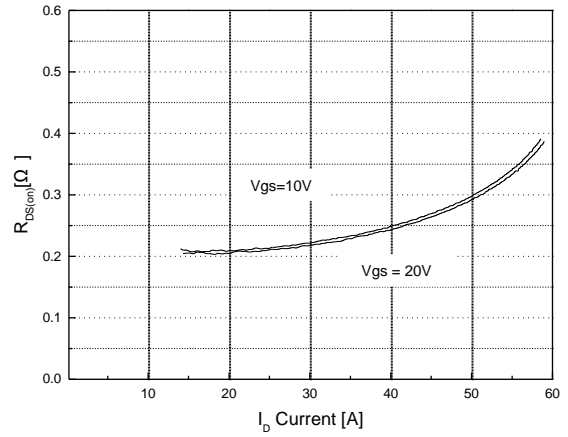


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

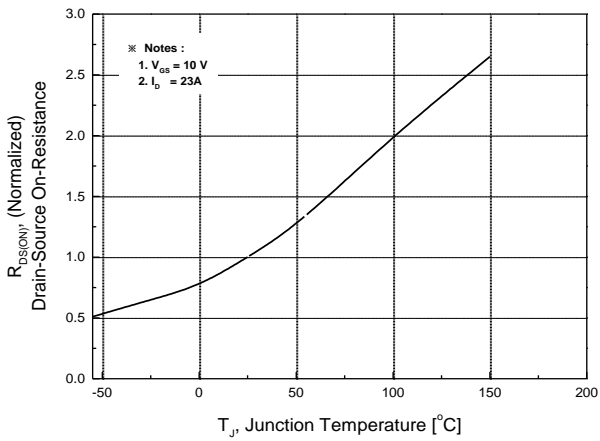


Fig.3 On-Resistance Variation with Temperature

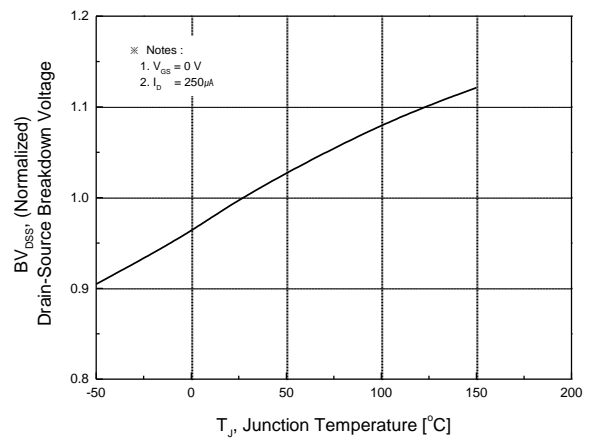


Fig.4 Breakdown Voltage Variation vs. Temperature

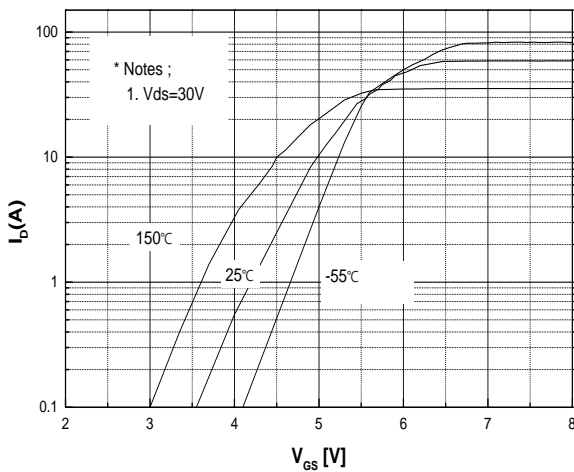


Fig.5 Transfer Characteristics

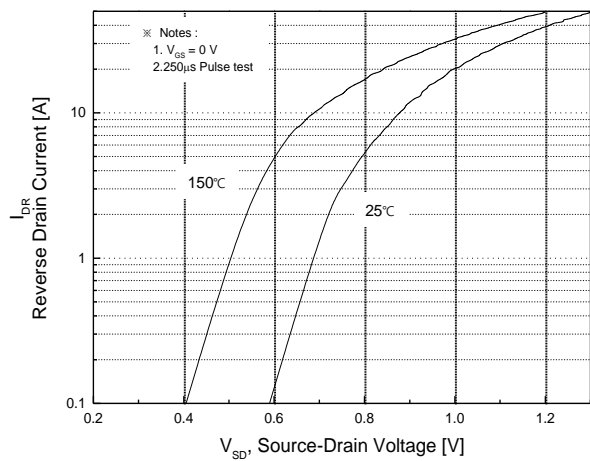


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

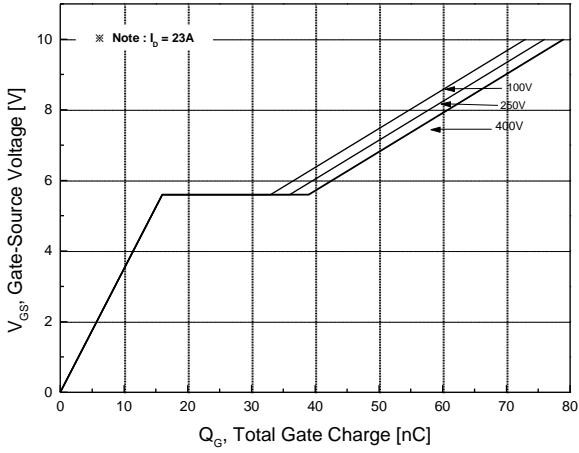


Fig.7 Gate Charge Characteristics

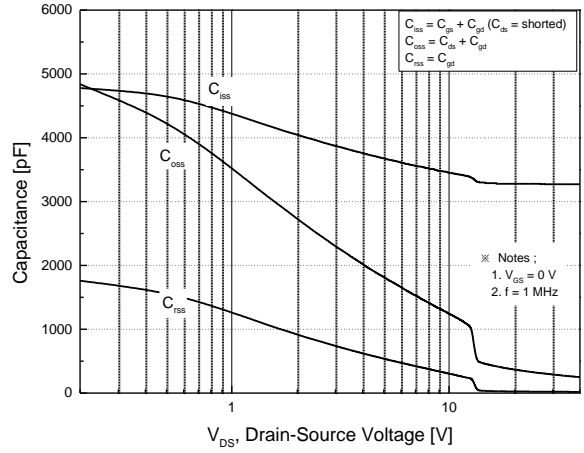


Fig.8 Capacitance Characteristics

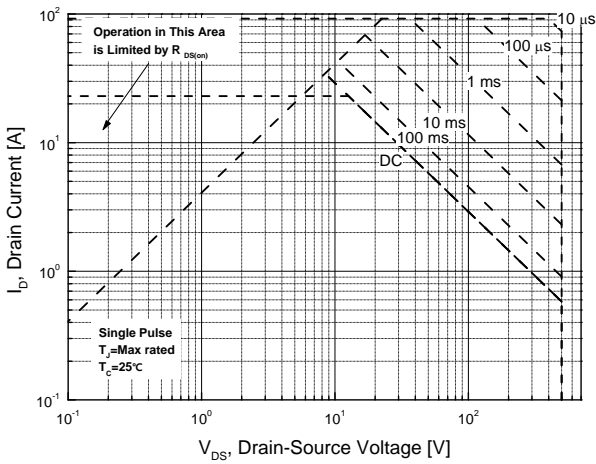


Fig.9 Maximum Safe Operating Area

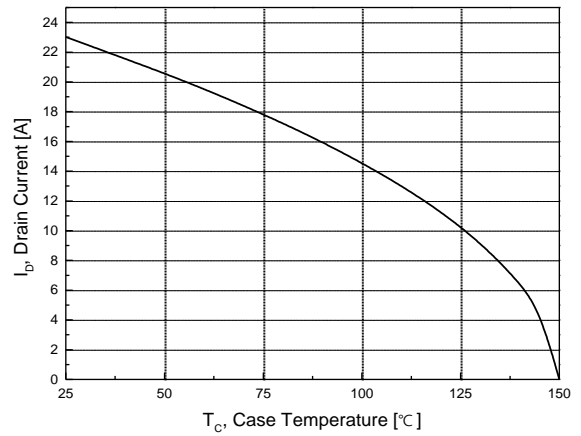


Fig.10 Maximum Drain Current vs. Case Temperature

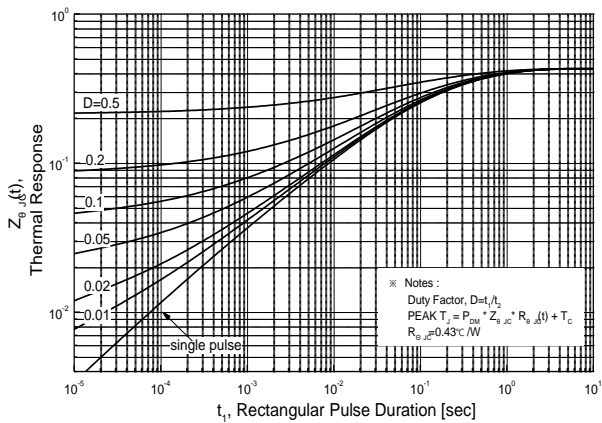


Fig.11 Transient Thermal Response Curve

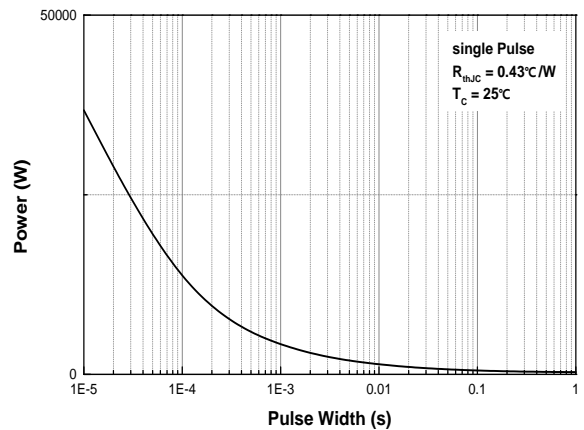
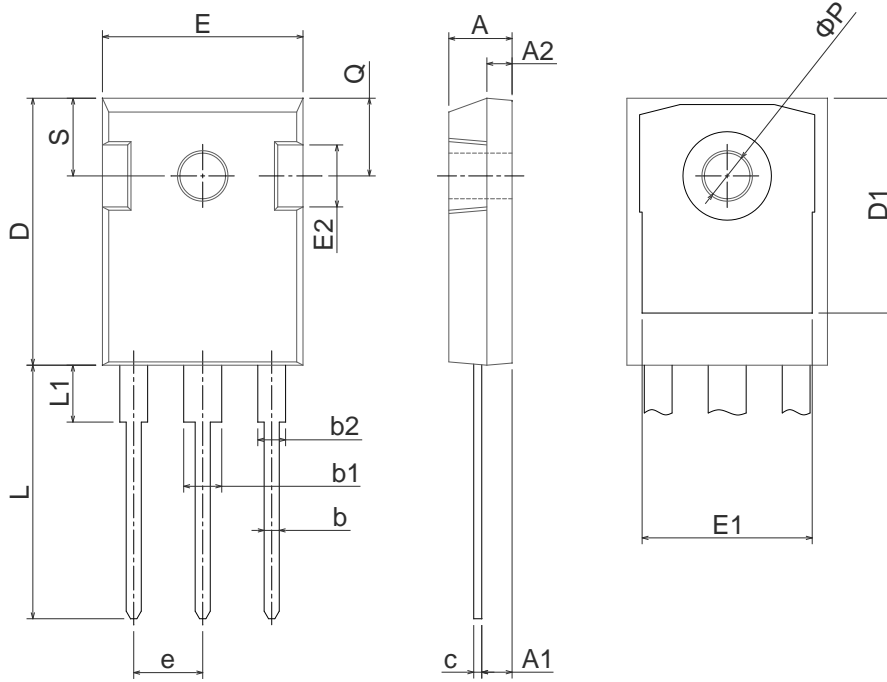


Fig.12 Single Pulse Maximum Power Dissipation

Physical Dimension

TO-247

Dimensions are in millimeters, unless otherwise specified




| Dimension | Min(mm) | Max(mm) |
|-----------|---------|---------|
| A | 4.70 | 5.31 |
| A1 | 2.20 | 2.60 |
| A2 | 1.50 | 2.49 |
| b | 0.99 | 1.40 |
| b1 | 2.59 | 3.43 |
| b2 | 1.65 | 2.39 |
| c | 0.38 | 0.89 |
| D | 20.30 | 21.46 |
| D1 | 13.08 | - |
| E | 15.45 | 16.26 |
| E1 | 13.06 | 14.02 |
| E2 | 4.32 | 5.49 |
| e | 5.45BSC | |
| L | 19.81 | 20.57 |
| L1 | - | 4.50 |
| ΦP | 3.50 | 3.70 |
| Q | 5.38 | 6.20 |
| S | 6.15BSC | |

Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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